

U.S.S.N. 09/995,031

In The Claims

Claim 1 has been amended as follows:

1. (Twice Amended) A metal oxide semiconductor (MOS) device comprising:

a semi-conducting substrate having source and drain regions;

a gate dielectric layer of less than 100 Å thickness on said semi-conducting substrate; and

a gate formed of a metal selected from the group consisting of Re and Rh on top of said gate dielectric layer.

Claim 10 has been amended as follows:

10. (Twice Amended) A field effect transistor (FET) comprising:

a semi-conducting substrate having at least one source and one drain region;

a gate dielectric layer of less than 100 Å thickness on the semi-conducting substrate; and

a gate formed of a metal selected from the group consisting of Re and Rh on top of the gate dielectric layer.